

NPN general purpose transistors

BC107; BC108; BC109

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 45 V).

APPLICATIONS

- General purpose switching and amplification.

DESCRIPTION

NPN transistor in a TO-18; SOT18 metal package.
PNP complement: BC177..

PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	collector, connected to the case

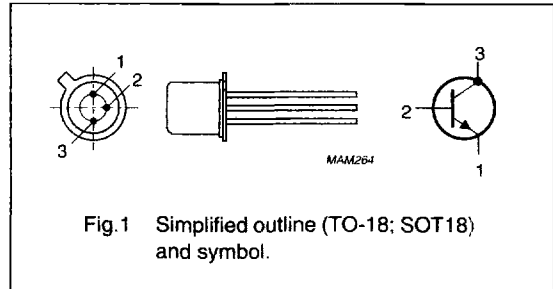


Fig. 1 Simplified outline (TO-18; SOT18) and symbol.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	BC107		–	50	V
	BC108; BC109		–	30	V
V_{CEO}	collector-emitter voltage	open base			
	BC107		–	45	V
	BC108; BC109		–	20	V
I_{CM}	peak collector current		–	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^{\circ}\text{C}$	–	300	mW
h_{FE}	DC current gain	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$			
	BC107		110	450	
	BC108		110	800	
	BC109		200	800	
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	100	–	MHz

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

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V_{CBO}	collector-base voltage	open emitter			
	BC107		–	50	V
	BC108; BC109		–	30	V
V_{CEO}	collector-emitter voltage	open base			
	BC107		–	45	V
	BC108; BC109		–	20	V
V_{EBO}	emitter-base voltage	open collector			
	BC107		–	6	V
	BC108; BC109		–	5	V
I_C	collector current (DC)		–	100	mA
I_{CM}	peak collector current		–	200	mA
I_{BM}	peak base current		–	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$	–	300	mW
T_{stg}	storage temperature		–65	+150	$^\circ\text{C}$
T_j	junction temperature		–	175	$^\circ\text{C}$
T_{amb}	operating ambient temperature		–65	+150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	0.5	K/mW
$R_{th\ j-c}$	thermal resistance from junction to case		0.2	K/mW

Note

1. Transistor mounted on an FR4 printed-circuit board.

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CHARACTERISTICS

$T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 20\text{ V}$	–	–	15	nA
		$I_E = 0; V_{CB} = 20\text{ V}; T_j = 150\text{ }^\circ\text{C}$	–	–	15	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	–	50	nA
h_{FE}	DC current gain BC107A; BC108A BC107B; BC108B; BC109B BC108C; BC109C	$I_C = 10\text{ }\mu\text{A}; V_{CE} = 5\text{ V}$	–	90	–	
			40	150	–	
			100	270	–	
h_{FE}	DC current gain BC107A; BC108A BC107B; BC108B; BC109B BC108C; BC109C	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$	110	180	220	
			200	290	450	
			420	520	800	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	–	90	250	mV
		$I_C = 100\text{ mA}; I_B = 5\text{ mA}$	–	200	600	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}; \text{note 1}$	–	700	–	mV
		$I_C = 100\text{ mA}; I_B = 5\text{ mA}; \text{note 1}$	–	900	–	mV
V_{BE}	base-emitter voltage	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}; \text{note 2}$	550	620	700	mV
		$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; \text{note 2}$	–	–	770	mV
C_c	collector capacitance	$I_E = I_B = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	2.5	6	pF
C_e	emitter capacitance	$I_C = I_C = 0; V_{EB} = 0.5\text{ V}; f = 1\text{ MHz}$	–	9	–	pF
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CB} = 5\text{ V}; f = 100\text{ MHz}$	100	–	–	MHz
F	noise figure BC109B; BC109C	$I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; R_S = 2\text{ k}\Omega;$ $f = 30\text{ Hz to }15.7\text{ kHz}$	–	–	4	dB
			–	–	–	
F	noise figure BC107A; BC108A BC107B; BC108B; BC108C BC109B; BC109C	$I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; R_S = 2\text{ k}\Omega;$ $f = 1\text{ kHz}; B = 200\text{ Hz}$	–	–	10	dB
			–	–	–	
			–	–	4	dB

Notes

- V_{BEsat} decreases by about 1.7 mV/K with increasing temperature.
- V_{BE} decreases by about 2 mV/K with increasing temperature.